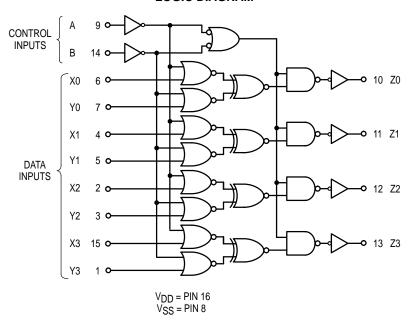
# 4-Bit AND/OR Selector or Quad 2-Channel Data Selector or Quad Exclusive "NOR" Gate

The MC14519B is constructed with MOS P-channel and N-channel enhancement mode devices in a monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired.

This device provides three functions in one package; a 4–Bit AND/OR Selector, a Quad 2–Channel Data Selector, or a Quad Exclusive NOR Gate.

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range
- Plug-in Replacement for CD4019 in Most Applications

#### **LOGIC DIAGRAM**



# MC14519B



L SUFFIX CERAMIC CASE 620



P SUFFIX PLASTIC CASE 648



D SUFFIX SOIC CASE 751B

#### **ORDERING INFORMATION**

MC14XXXBCP Plastic MC14XXXBCL Ceramic MC14XXXBD SOIC

 $T_A = -55^{\circ}$  to 125°C for all packages.

#### **TRUTH TABLE**

Contro	I Inputs	Output
Α	zn	
0	0	0
0	1	Yn
1	0	Xn
1	1	$x_n \odot Y_n$

NOTE:  $X_n \odot Y_n$  means  $X_n$  (Exclusive–NOR)  $Y_n$ 

### MAXIMUM RATINGS\* (Voltages Referenced to VSS)

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	DC Supply Voltage	- 0.5 to + 18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage (DC or Transient)	– 0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient), per Pin	± 10	mA
PD	Power Dissipation, per Package†	500	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

<sup>\*</sup> Maximum Ratings are those values beyond which damage to the device may occur. †Temperature Derating:

Plastic "P and D/DW" Packages: -7.0 mW/°C From  $65^{\circ}$ C To  $125^{\circ}$ C Ceramic "L" Packages: -12 mW/°C From  $100^{\circ}$ C To  $125^{\circ}$ C

#### **PIN ASSIGNMENT** 16 \ V<sub>DD</sub> X2 [ 15 X3 Y2 🛚 3 14 🛮 B X1 🛮 4 13 Z3 Y1 🛮 5 12 Z2 X0 ☐ 6 11 🛭 Z1 Y0 🛮 7 10 Z0 9 🛮 A V<sub>SS</sub> □ 8

### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

		V <sub>DD</sub>	- 5	5°C		25°C		125	5°C	
Characteristic	Symbol	Vdc	Min	Max	Min	Typ #	Max	Min	Max	Unit
Output Voltage "0" Level Vin = VDD or 0	VOL	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or $V_{DD}$ "1" Level	VOH	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	  -  -	4.95 9.95 14.95	  -  -	Vdc
Input Voltage "0" Level (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	V <sub>IL</sub>	5.0 10 15	_ _ _	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
"1" Level (V <sub>O</sub> = 0.5 or 4.5 Vdc) (V <sub>O</sub> = 1.0 or 9.0 Vdc) (V <sub>O</sub> = 1.5 or 13.5 Vdc)	VIH	5.0 10 15	3.5 7.0 11	_ _ _	3.5 7.0 11	2.75 5.50 8.25	_ _ _	3.5 7.0 11	_ _ _	Vdc
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) Source (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	ІОН	5.0 5.0 10 15	- 3.0 - 0.64 - 1.6 - 4.2	_ _ _ _	- 2.4 - 0.51 - 1.3 - 3.4	- 4.2 - 0.88 - 2.25 - 8.8	_ _ _ _	- 1.7 - 0.36 - 0.9 - 2.4	_ _ _ _	mAdc
(V <sub>OL</sub> = 0.4 Vdc) Sink (V <sub>OL</sub> = 0.5 Vdc) (V <sub>OL</sub> = 1.5 Vdc)	l <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	_ _ _	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current	l <sub>in</sub>	15	_	± 0.1	_	±0.00001	± 0.1	_	± 1.0	μAdc
Input Capacitance (Vin = 0)	C <sub>in</sub>	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0 10 15	_ _ _	5.0 10 20	_ _ _	0.005 0.010 0.015	5.0 10 20	_ _ _	150 300 600	μAdc
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C <sub>L</sub> = 50 pF on all outputs, all buffers switching)	lΤ	5.0 10 15			$I_T = (2$	.2 μA/kHz) f 2.4 μA/kHz) f 3.6 μA/kHz) f	+ IDD			μAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I<sub>T</sub> is in  $\mu$ A (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> – V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.004.

<sup>\*\*</sup> The formulas given are for the typical characteristics only at 25  $^{\circ}\text{C}.$ 

<sup>†</sup>To calculate total supply current at loads other than 50 pF:

## **SWITCHING CHARACTERISTICS\*** ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ )

Characteristic	Symbol	V <sub>DD</sub>	Min	Тур#	Max	Unit
Output Rise and Fall Time  t <sub>TLH</sub> , t <sub>THL</sub> = (1.5 ns/pF) C <sub>L</sub> + 25 ns  t <sub>TLH</sub> , t <sub>THL</sub> = (0.75 ns/pF) C <sub>L</sub> + 12.5 ns  t <sub>TLH</sub> , t <sub>THL</sub> = (0.55 ns/pF) C <sub>L</sub> + 9.5 ns	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15		100 50 40	200 100 80	ns
Propagation Delay Time  tplh, tphl = (1.7 ns/pF) C <sub>L</sub> + 165 ns  tplh, tphl = (0.66 ns/pF) C <sub>L</sub> + 82  tplh, tphl = (0.5 ns/pF) C <sub>L</sub> + 65 ns	tpLH, <sup>t</sup> PHL	5.0 10 15	_ _ _	250 115 90	500 225 165	ns

<sup>\*</sup> The formulas given are for the typical characteristics only at 25°C.

<sup>#</sup>Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

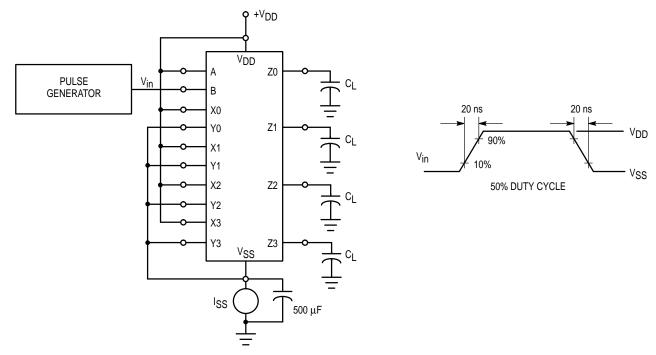


Figure 1. Dynamic Power Dissipation Test Circuit and Waveform

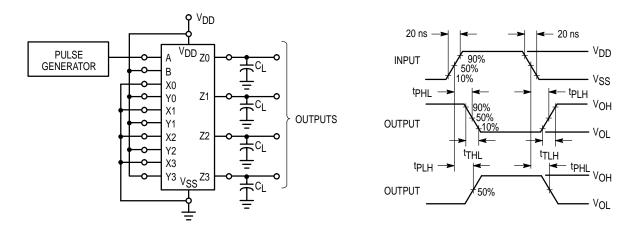
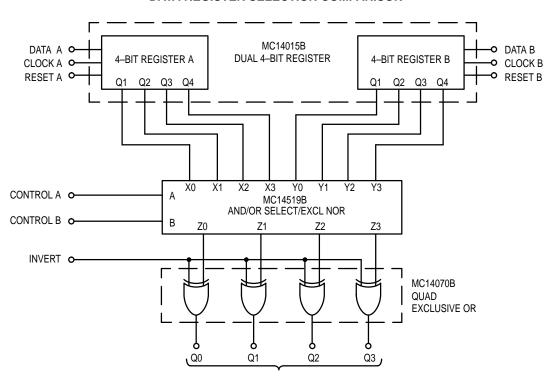


Figure 2. Switching Time Test Circuit and Waveforms

### **TYPICAL CIRCUIT APPLICATIONS**

#### **DATA REGISTER SELECTION COMPARISON**



#### **CONVERSION TABLE**

Ор	Operation Code			Out			
Α	В	INV	Q0	Q1	Q2	Q3	Function
0	0	0	0	0	0	0	Inhibit, all zeros
0	0	1	1	1	1	1	Inhibit, all ones
1	0	0	X0	X1	X2	Х3	Control A
1	0	1	<b>⊼</b> 0	<del>X</del> 1	<b>⊼</b> 2	<b></b> ₹3	Control A and Invert
0	1	0	Y0	Y1	Y2	Y3	Control B
0	1	1	<u></u> 70	<u>\( \bar{Y} \) 1</u>	<u>₹</u> 2	₹3	Control B and Invert
1	1	0	X0 ⊙ Y0	X1 ⊙ Y1	X2 ⊙ Y2	X3 ⊙ Y3	Exclusive NOR
1	1	1	X0 ⊕ Y0	X1 ⊕ Y1	X2 ⊕ Y2	X3 ⊕ Y3	Exclusive OR

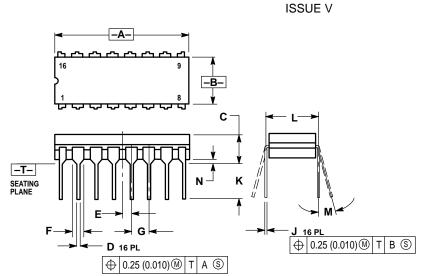
This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must

be left open.

### **OUTLINE DIMENSIONS**

# **L SUFFIX** CERAMIC DIP PACKAGE CASE 620-10



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

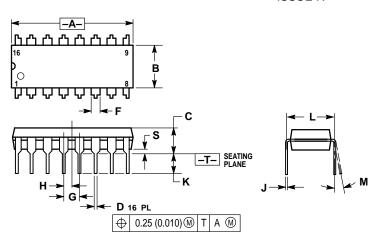
  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

  4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC RODY.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.750	0.785	19.05	19.93
В	0.240	0.295	6.10	7.49
С		0.200		5.08
D	0.015	0.020	0.39	0.50
Е	0.050	BSC	1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100	BSC	2.54 BSC	
Н	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300	0.300 BSC		BSC
М	0 °	15°	0 °	15°
N	0.020	0.040	0.51	1.01

#### **P SUFFIX**

PLASTIC DIP PACKAGE CASE 648-08 ISSUE R



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10°	0°	10 °	
S	0.020	0.040	0.51	1.01	

#### **OUTLINE DIMENSIONS**



- DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

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